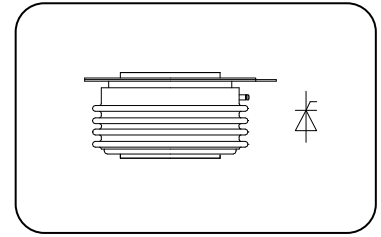




Features:

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses
- Short turn-off time
- Hermetic metal cases with ceramic insulators

$I_{T(AV)}$ 1000A
 V_{DRM}/V_{RRM} 1100~1400V
 t_q 10~16 μ s
 I_{TSM} 16.3kA



Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters
- AC motor speed control
- General power switching applications

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		$T_j(^{\circ}C)$	VALUE			UNIT
					Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled,	$T_c=55^{\circ}C$	125		1000	1260	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM} \& V_{RRM}, t_p=10ms$ $V_{DSM} \& V_{RSM} = V_{DRM} \& V_{RRM} + 100V$		125	1100		1400	V
I_{DRM} I_{RRM}	Repetitive peak off-state current Repetitive peak reverse current	$V_D = V_{DRM}$ $V_R = V_{RRM}$		125			80	mA
I_{TSM}	Surge on-state current	10ms half sine wave		125			16.3	kA
I^2t	I^2t for fusing coordination	$V_R = 0.6V_{RRM}$					1328	$A^2s \cdot 10^3$
V_{TO}	Threshold voltage			125			1.65	V
r_T	On-state slop resistance						0.36	m Ω
V_{TM}	Peak on-state voltage	$I_{TM}=3000A, F=24kN$		25			3.20	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$		125			1000	V/ μ s
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}, I_{TM}=(2-3)I_{T(AV)}, t=5s,$ Gate pulse $t_r \leq 0.5\mu s, I_{GM}=1.5A, f=50Hz$		125			600	A/ μ s
Q_{rr}	Recovery charge	$I_{TM}=1000A, t_p=1000\mu s,$ $di/dt=-20A/\mu s, V_R=100V$		125		87	100	μC
t_q	Circuit commutated turn-off time	$I_{TM}=1000A, t_p=1000\mu s, V_R=100V$ $dv/dt=30V/\mu s, di/dt=-20A/\mu s$		125	10		16	μs
I_{GT}	Gate trigger current	$V_A=12V, I_A=1A$		25	30		250	mA
V_{GT}	Gate trigger voltage				0.8		3.0	V
I_H	Holding current				20		400	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$		125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 24kN					0.020	$^{\circ}C/W$
$R_{th(c-h)}$	Thermal resistance case to heat sink						0.005	
F_m	Mounting force				19		26	kN
T_{stg}	Stored temperature				-40		140	$^{\circ}C$
W_i	Weight					470		g
Outline	KT55cT							

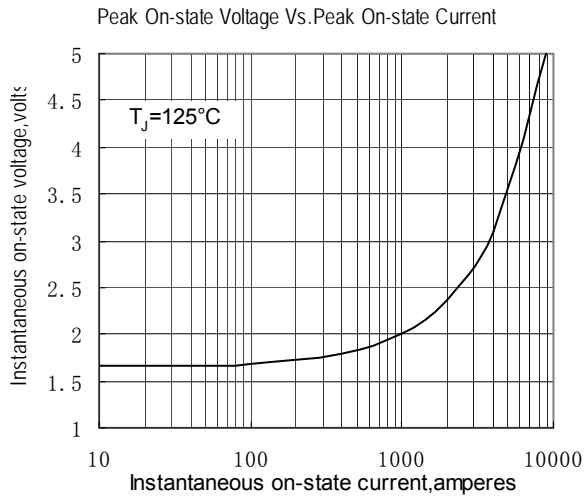


Fig.1

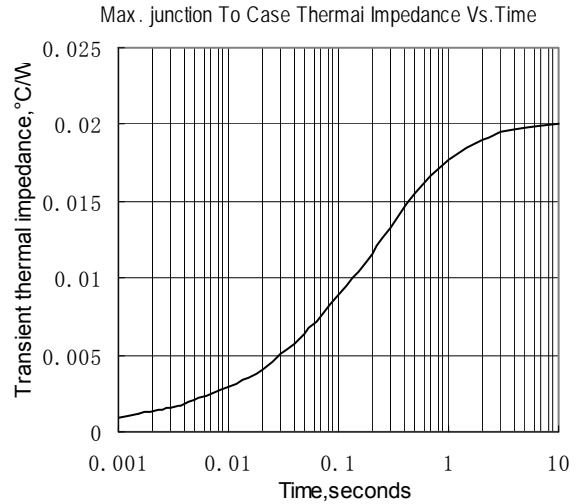


Fig.2

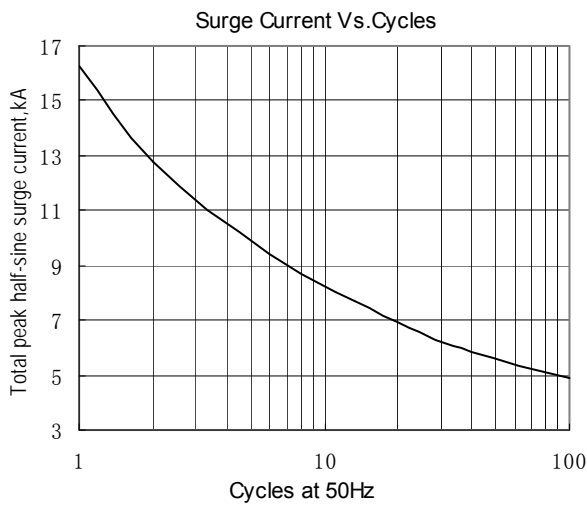


Fig.3

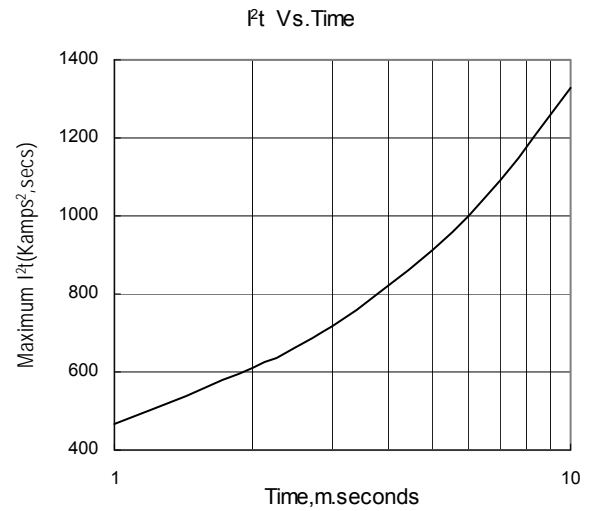


Fig.4

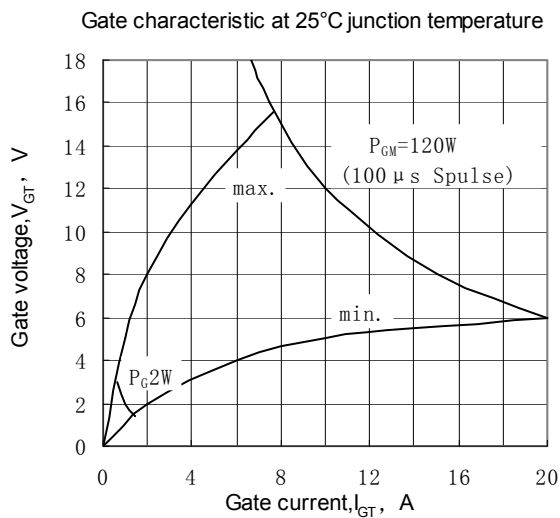


Fig.5

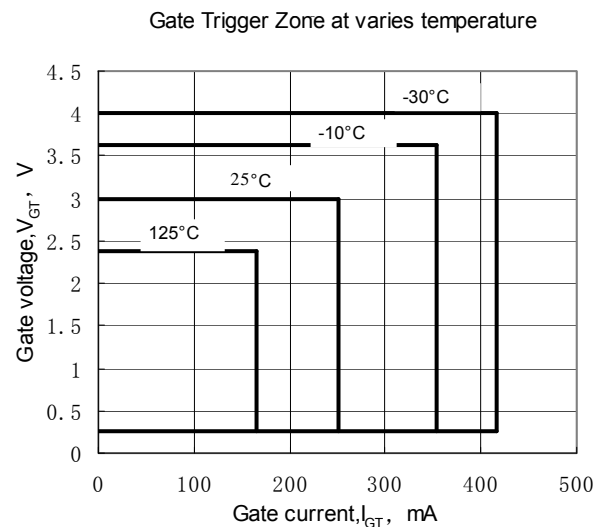
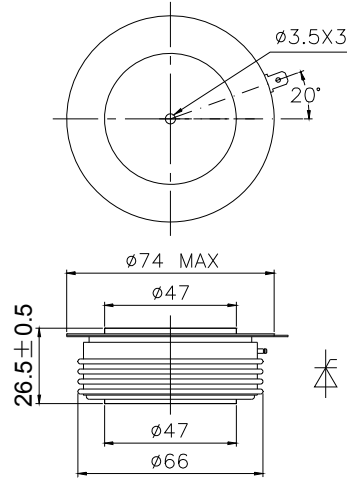


Fig.6



Outline:

图8-KT55cT



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